Amendments to the Claims

Claims 1-65 (Canceled).

66. (Currently Amended): A method of forming a capacitor, comprising:

depositing a ~~container forming layer~~ container-forming layer over a substrate;

depositing a ~~carbon containing masking layer~~ carbon-containing masking layer over the container forming layer;

patterning the masking layer to comprise a plurality of circular shaped container openings therein having minimum diameter of less than or equal to 0.20 micron;

plasma etching the ~~container forming layer~~ container-forming layer through the masking layer openings using conditions effective to both a) etch the masking layer to modify the shape of the masking layer openings from circular to having at least four straight line segments of at least 2 nanometers long, and b) form container openings in the ~~container forming layer~~ container-forming layer of the modified shapes; and

forming capacitors comprising container shapes using the container openings in the ~~container forming layer~~ container-forming layer.

67. (Original): The method of claim 66 wherein the plasma etching forms the modified shapes to be squares.

68. (Original): The method of claim 66 wherein the plasma etching forms the modified shapes to be hexagons.

69. (Original): The method of claim 66 wherein the patterning comprises photolithography and solvent etch.

70. (Original): The method of claim 66 wherein the container openings are patterned to have minimum feature dimensions of less than 0.15 micron.

71. (Original): The method of claim 66 comprising fabricating the capacitor as part of DRAM circuitry.

72. (Original): The method of claim 66 wherein the conditions comprise plasma etching using a total applied power of at least $7W/cm^2$ of substrate area being processed.

73. (Original): The method of claim 66 wherein the conditions comprise plasma etching using a total applied power of at least 10W/cm^2 of substrate area being processed.

74. (Original): The method of claim 66 wherein the conditions comprise plasma etching using a substrate temperature of at least 40°C.

75. (Original): The method of claim 66 wherein the conditions comprise plasma etching using a total applied power of at least 7W/cm^2 of substrate area being processed, and using a substrate temperature of at least 40°C.

76. (Original): The method of claim 66 wherein the conditions comprise a fluorocarbon comprising etching chemistry.

77. (Original): The method of claim 66 wherein the conditions comprise plasma etching using a total applied power of at least 7W/cm^2 of substrate area being processed, using a substrate temperature of at least 40°C, and a fluorocarbon comprising etching chemistry.

78. (Original): The method of claim 66 wherein the conditions comprise plasma etching in a capacitively coupled, multi frequency plasma etcher.

79. (Original): The method of claim 78 wherein multiple frequencies are applied to a wafer chuck upon which the substrate rests during etching.

80. (Original): The method of claim 79 wherein the plasma etching uses a total applied power of at least $7W/cm^2$ of substrate area being processed to the wafer chuck, uses a substrate temperature of at least 40°C, and a fluorocarbon comprising etching chemistry.

81. (Original): The method of claim 78 wherein one frequency is applied to a wafer chuck upon which the substrate rests during etching and another frequency is applied to an electrode spaced from the substrate.